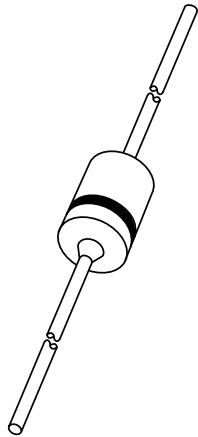


DATA SHEET



1N914; 1N914A; 1N914B High-speed diodes

Product specification
Supersedes data of 1999 May 26

2003 Jun 06

High-speed diodes

1N914; 1N914A; 1N914B

FEATURES

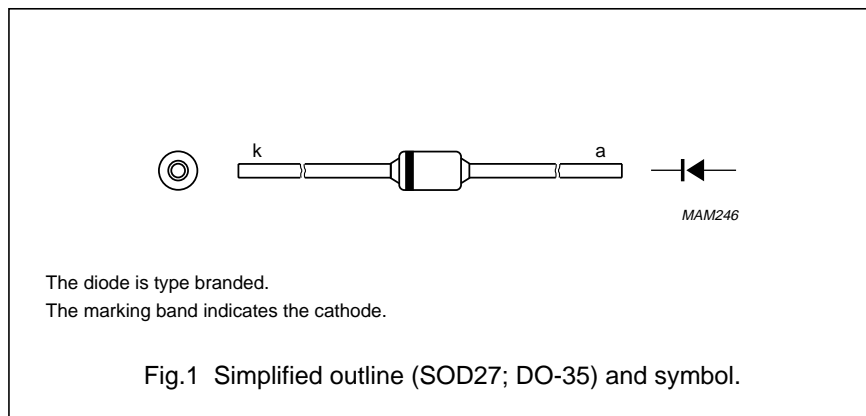
- Hermetically sealed leaded glass SOD27 (DO-35) package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 225 mA.

APPLICATIONS

- High-speed switching.

DESCRIPTION

The 1N914, 1N914A and 1N914B are high-speed switching diodes fabricated in planar technology, and encapsulated in a hermetically sealed leaded glass SOD27 (DO-35) package.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	100	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	see Fig.2; note 1	–	75	mA
I_{FRM}	repetitive peak forward current		–	225	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\ \mu\text{s}$ $t = 1\ \text{ms}$ $t = 1\ \text{s}$	–	4 1 0.5	A A A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+200	°C
T_j	junction temperature		–	175	°C

Note

1. Device mounted on an FR4 printed-circuit board; lead length 10 mm.

High-speed diodes

1N914; 1N914A; 1N914B

ELECTRICAL CHARACTERISTICS $T_j = 25\text{ °C}$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_F	forward voltage	see Fig.3			
	1N914; 1N914A	$I_F = 10\text{ mA}$	–	1	V
	1N914B	$I_F = 5\text{ mA}$	0.62	0.72	V
	1N914B	$I_F = 100\text{ mA}$	–	1	V
I_R	reverse current	see Fig.5			
		$V_R = 20\text{ V}$	–	25	nA
		$V_R = 75\text{ V}$	–	5	μA
		$V_R = 20\text{ V}; T_j = 150\text{ °C}$	–	50	μA
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0$; see Fig.6	–	4	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\ \Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7	–	8	ns
		when switched from $I_F = 10\text{ mA}$ to $I_R = 60\text{ mA}$; $R_L = 100\ \Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7	–	4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 50\text{ mA}$; $t_r = 20\text{ ns}$; see Fig.8	–	2.5	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point	lead length 10 mm	240	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	lead length 10 mm; note 1	500	K/W

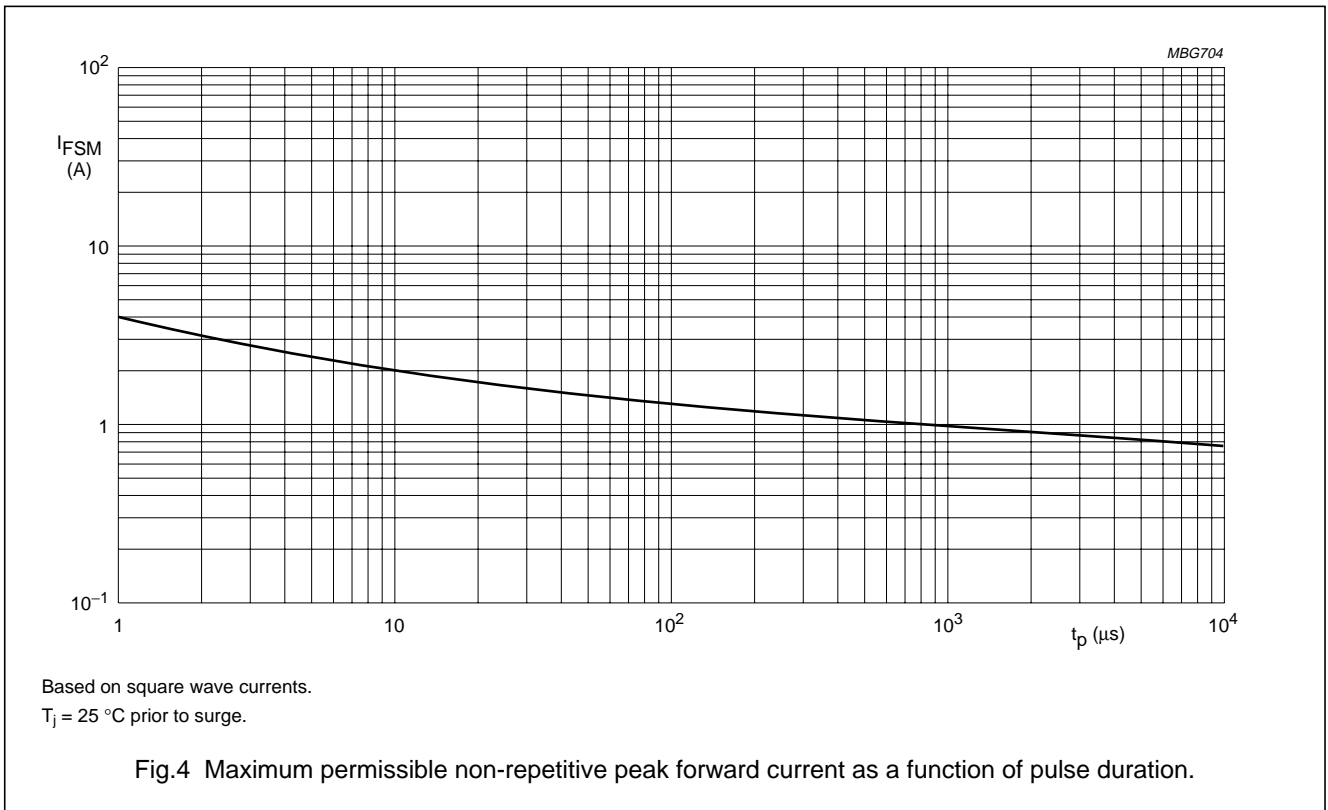
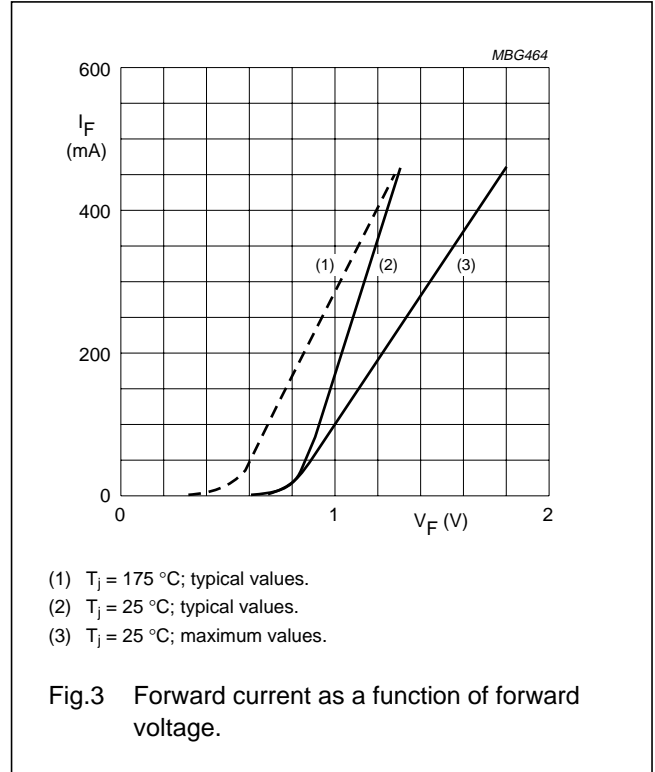
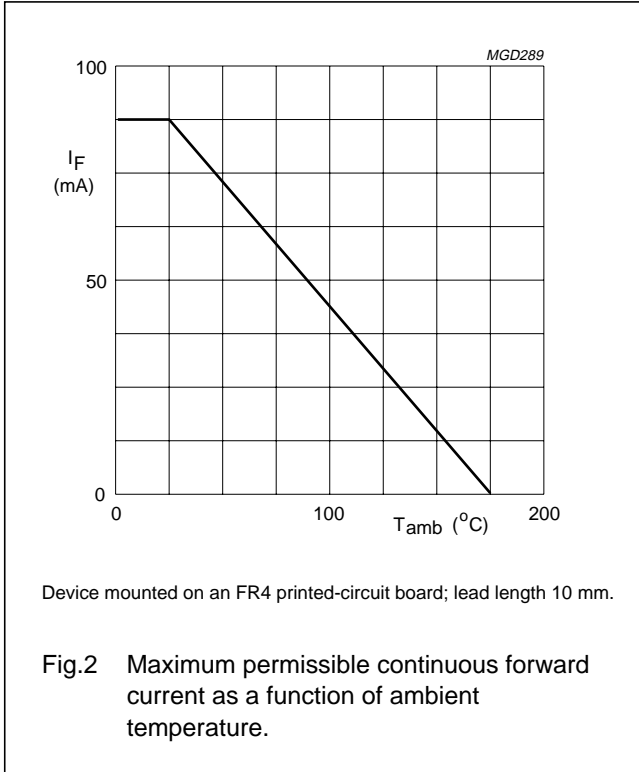
Note

1. Device mounted on a printed-circuit board without metallization pad.

High-speed diodes

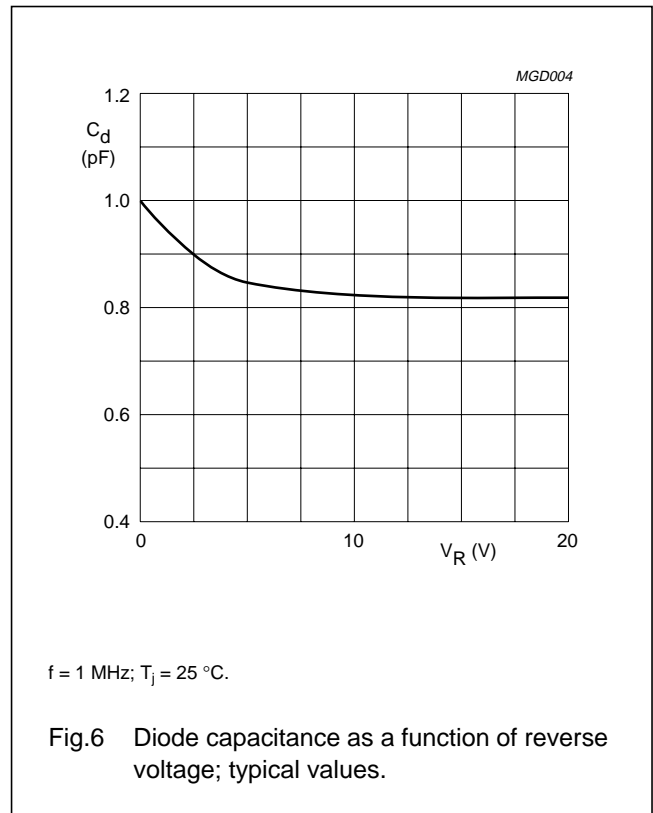
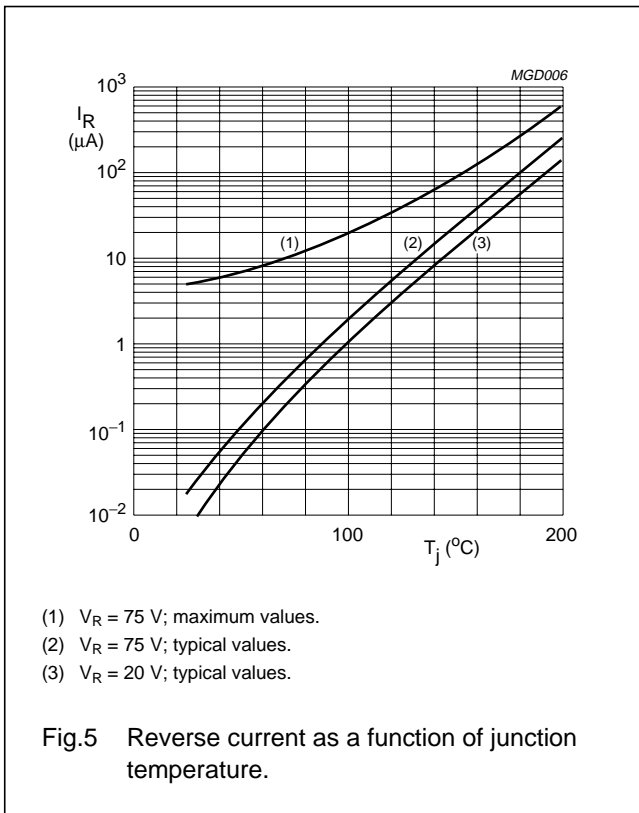
1N914; 1N914A; 1N914B

GRAPHICAL DATA



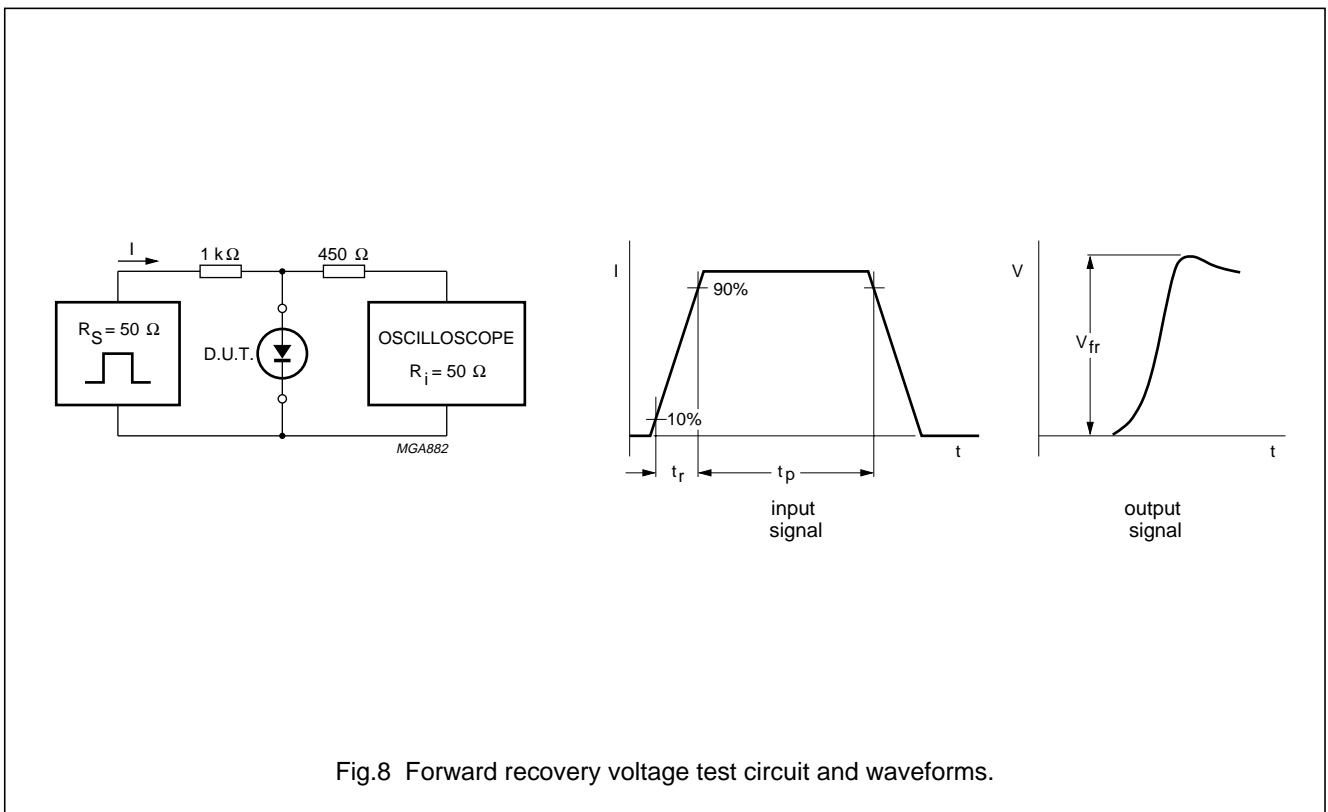
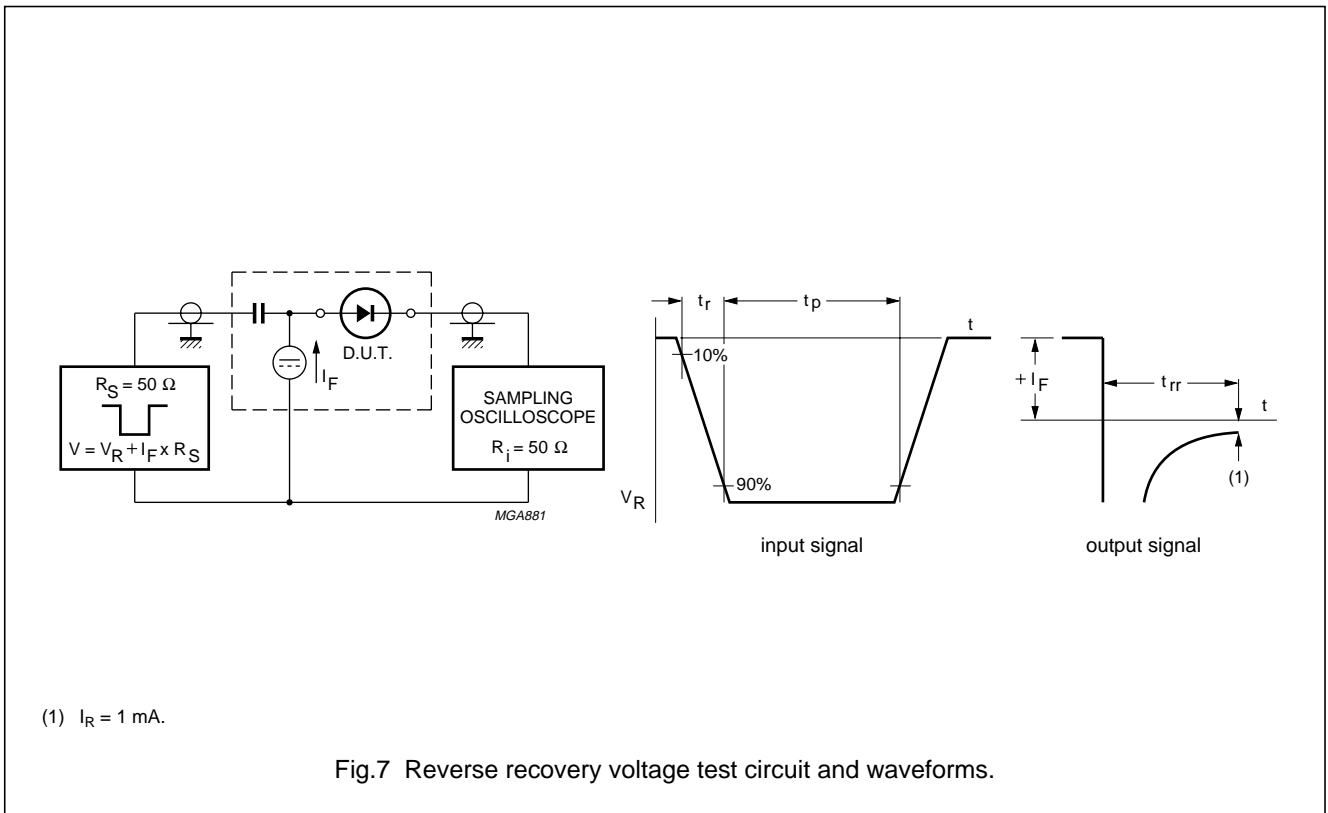
High-speed diodes

1N914; 1N914A; 1N914B



High-speed diodes

1N914; 1N914A; 1N914B



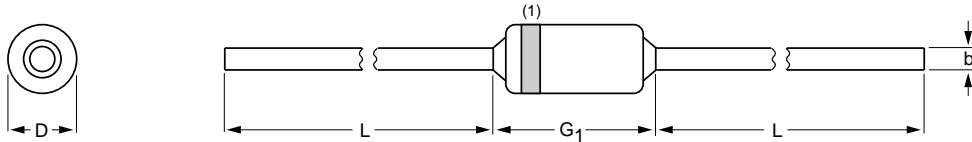
High-speed diodes

1N914; 1N914A; 1N914B

PACKAGE OUTLINE

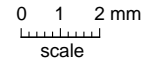
Hermetically sealed glass package; axial leaded; 2 leads

SOD27




DIMENSIONS (mm are the original dimensions)

UNIT	b max.	D max.	G ₁ max.	L min.
mm	0.56	1.85	4.25	25.4



Note

1. The marking band indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD27	A24	DO-35	SC-40			97-06-09

High-speed diodes

1N914; 1N914A; 1N914B

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Notes

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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High-speed diodes

1N914; 1N914A; 1N914B

NOTES

High-speed diodes

1N914; 1N914A; 1N914B

NOTES

High-speed diodes

1N914; 1N914A; 1N914B

NOTES

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